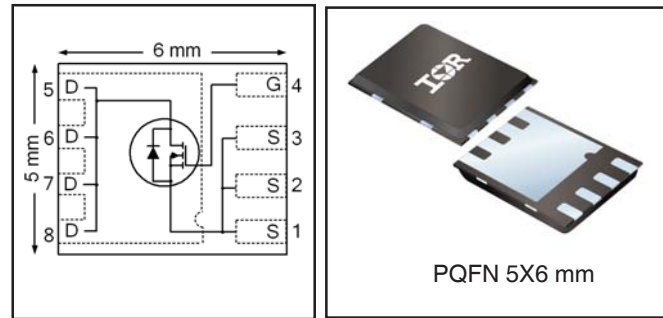


$V_{DS}$	<b>20</b>	<b>V</b>
$R_{DS(on) max}$ (@ $V_{GS} = 4.5V$ )	<b>0.99</b>	<b>m<math>\Omega</math></b>
(@ $V_{GS} = 2.5V$ )	<b>1.50</b>	
$Q_g$ (typical)	<b>155</b>	<b>nC</b>
$R_G$ (typical)	<b>1.3</b>	<b><math>\Omega</math></b>
$I_D$ (@ $T_{mb} = 25^\circ C$ )	<b>100<sup>Ⓞ</sup></b>	<b>A</b>

HEXFET<sup>®</sup> Power MOSFET



**Applications**

- Charge and discharge switch for battery application
- Load switch for 12V (typical) bus
- Hot-Swap Switch

**Features**

Low $R_{DSon}$ ( $\leq 0.99m\Omega$ )
Low Thermal Resistance to PCB ( $\leq 0.8^\circ C/W$ )
Low Profile ( $\leq 0.9$ mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free

**Benefits**

Lower Conduction Losses
Enable better thermal dissipation
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier

results in  
 ⇒

Base Part Number	Package Type	Standard Pack		Orderable part number	Note
		Form	Quantity		
IRFH6200PbF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH6200TRPbF	EOL Notice #259
	PQFN 5mm x 6mm	Tape and Reel	400	IRFH6200TR2PbF	

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	20	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	49	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	40	
$I_D @ T_{mb} = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	100 <sup>Ⓞ</sup>	
$I_D @ T_{mb} = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	100 <sup>Ⓞ</sup>	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	400	
$P_D @ T_A = 25^\circ C$	Power Dissipation <sup>②</sup>	3.6	W
$P_D @ T_{mb} = 25^\circ C$	Power Dissipation <sup>③</sup>	156	
	Linear Derating Factor <sup>⑤</sup>	0.029	W/ $^\circ C$
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Notes ① through ⑥ are on page 9

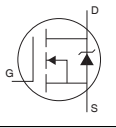
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	6.4	—	mV/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	0.75	0.95	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A ③
		—	0.80	0.99		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 50A ③
		—	1.10	1.50		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.5	0.8	1.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 150μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-6.6	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		—	—	150		V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -12V
g <sub>fs</sub>	Forward Transconductance	260	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 50A
Q <sub>g</sub>	Total Gate Charge	—	155	230	nC	V <sub>DS</sub> = 10V
Q <sub>gs</sub>	Gate-to-Source Charge	—	22	—		V <sub>GS</sub> = 4.5V
Q <sub>gd</sub>	Gate-to-Drain Charge	—	53	—		I <sub>D</sub> = 50A (See Fig.17 & 18)
R <sub>G</sub>	Gate Resistance	—	1.3	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	14	—	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V
t <sub>r</sub>	Rise Time	—	74	—		I <sub>D</sub> = 50A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	140	—		R <sub>G</sub> = 1.0Ω
t <sub>f</sub>	Fall Time	—	160	—		See Fig.15
C <sub>iss</sub>	Input Capacitance	—	10890	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	2890	—		V <sub>DS</sub> = 10V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	2180	—		f = 1.0MHz

**Avalanche Characteristics**

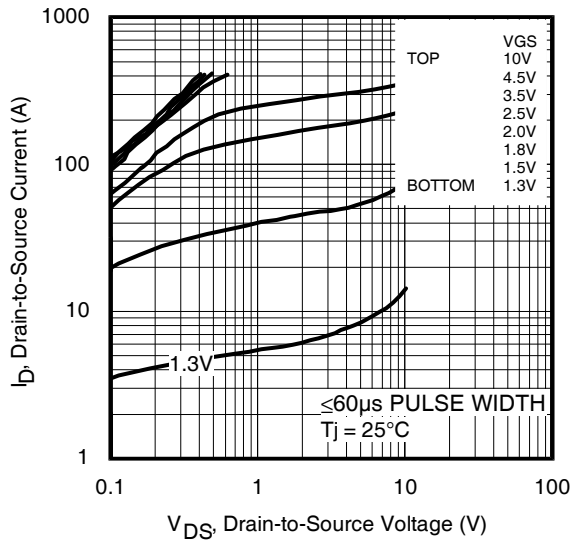
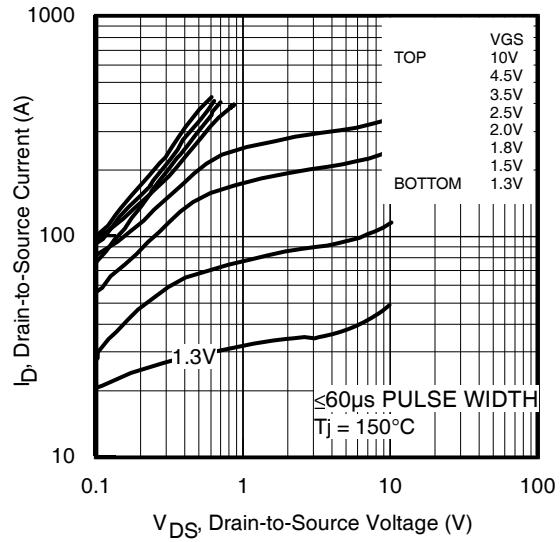
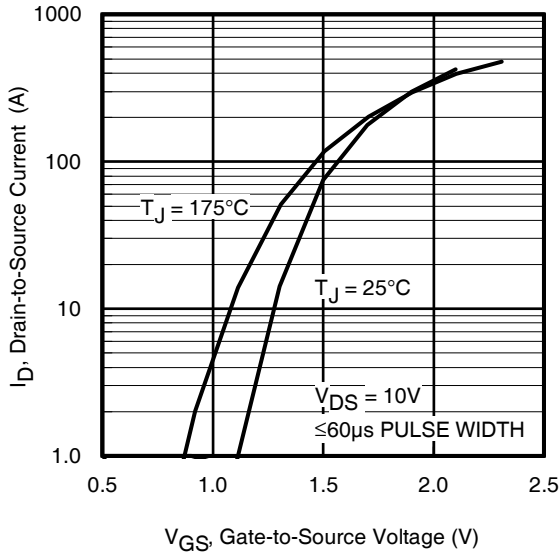
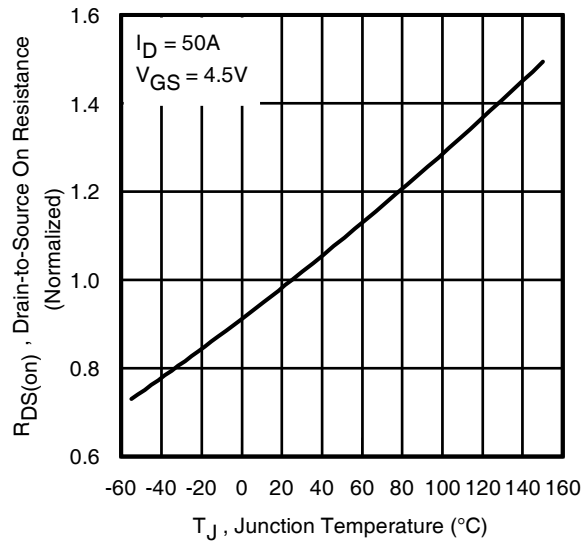
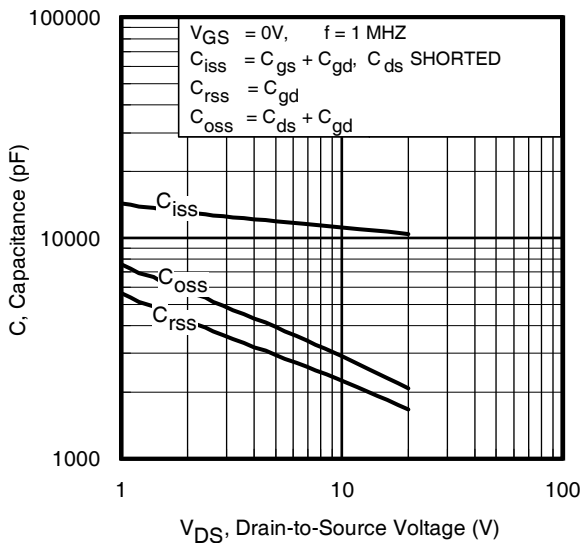
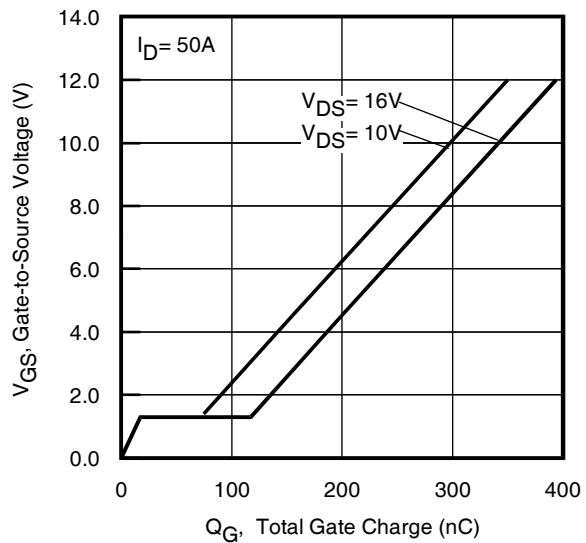
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	780	mJ
I <sub>AR</sub>	Avalanche Current ①	—	30	A

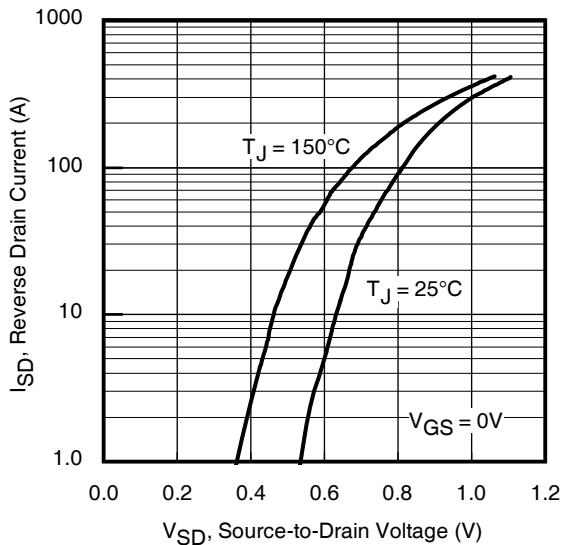
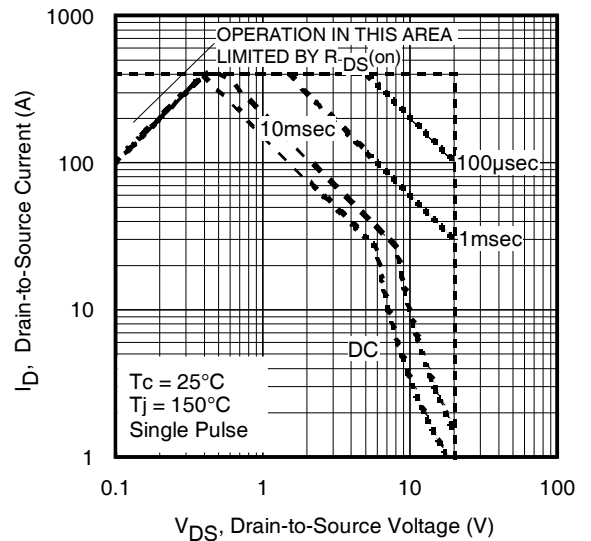
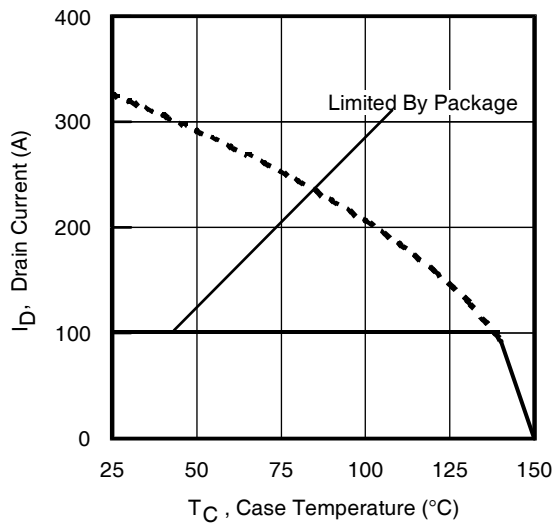
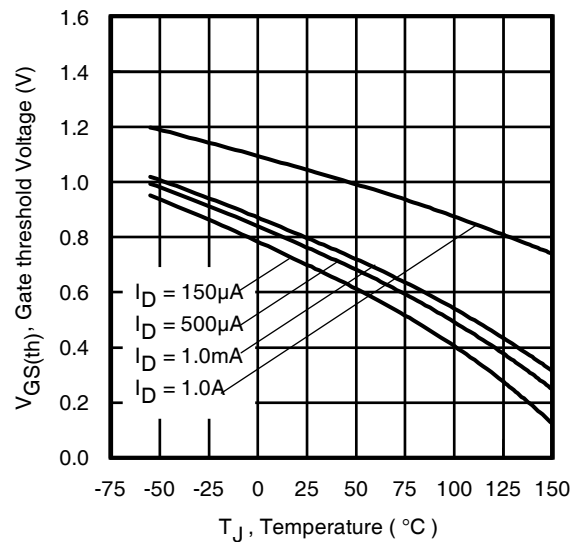
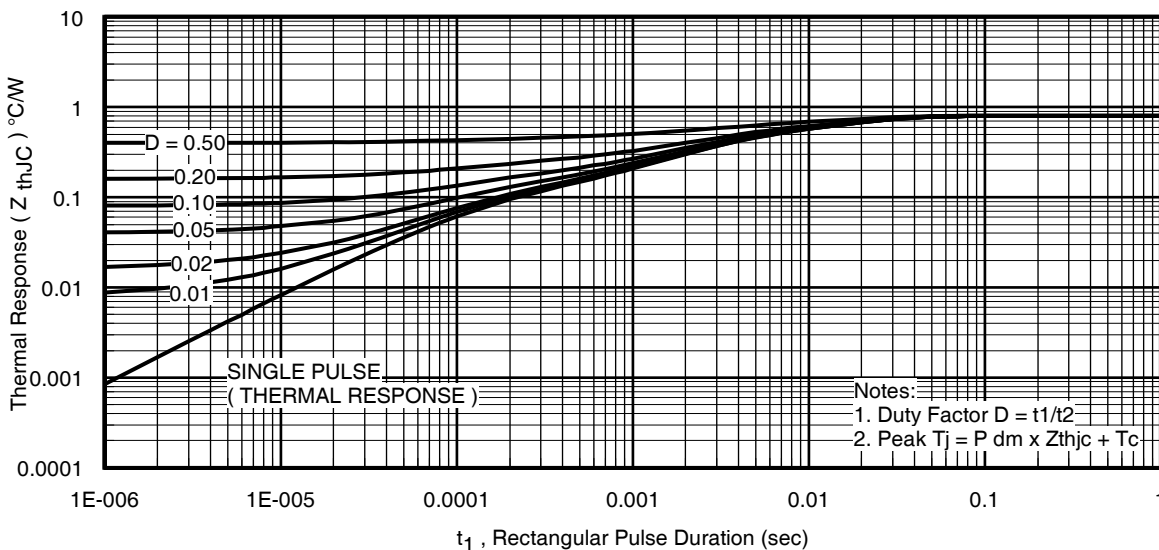
**Diode Characteristics**

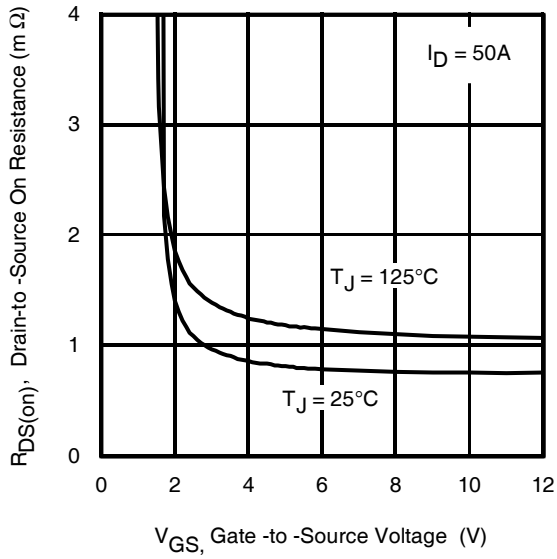
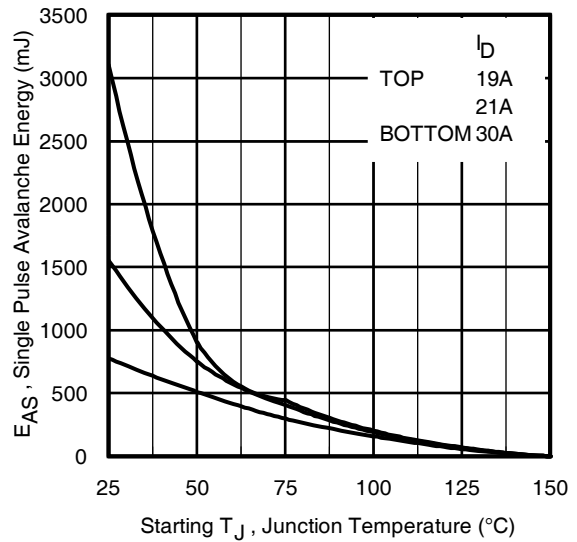
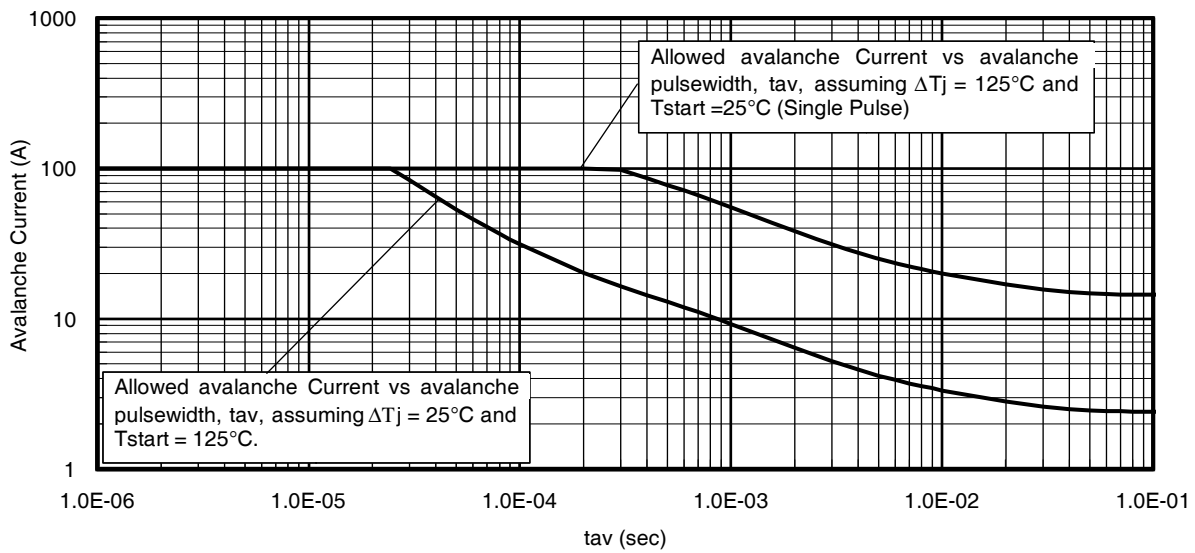
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	100	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	400		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 50A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	86	130	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 50A, V <sub>DD</sub> = 10V
Q <sub>rr</sub>	Reverse Recovery Charge	—	350	525	nC	di/dt = 260A/μs ③

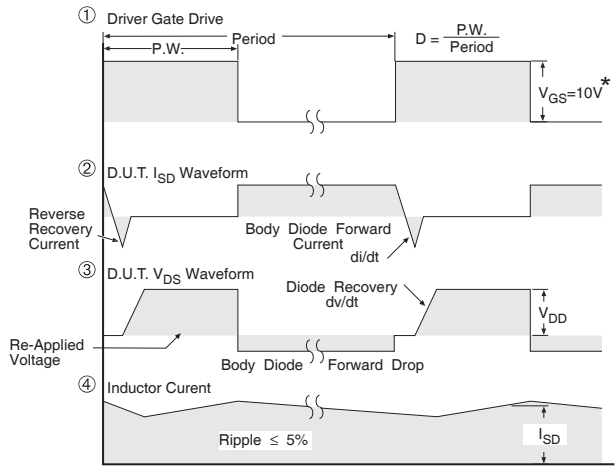
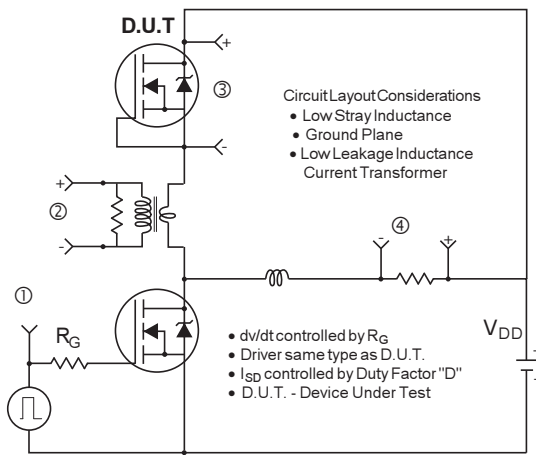
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC-mb</sub>	Junction-to-Mounting Base	0.5	0.8	°C/W
R <sub>θJC</sub> (Top)	Junction-to-Case ④	—	15	
R <sub>θJA</sub>	Junction-to-Ambient ⑤	—	35	
R <sub>θJA</sub> (<10s)	Junction-to-Ambient ⑤	—	22	


**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage**

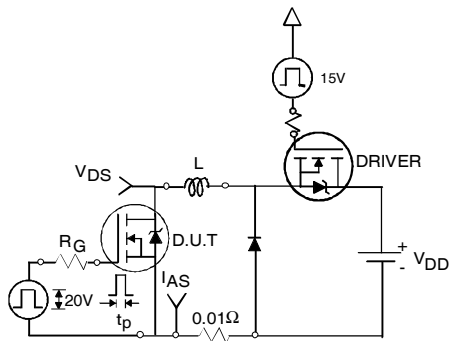

**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10.** Threshold Voltage vs. Temperature

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Mounting Base


**Fig 12.** On-Resistance vs. Gate Voltage

**Fig 13.** Maximum Avalanche Energy vs. Drain Current

**Fig 14.** Typical Avalanche Current vs. Pulsewidth

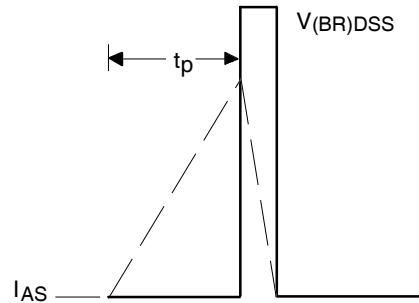


\*  $V_{GS} = 5V$  for Logic Level Devices

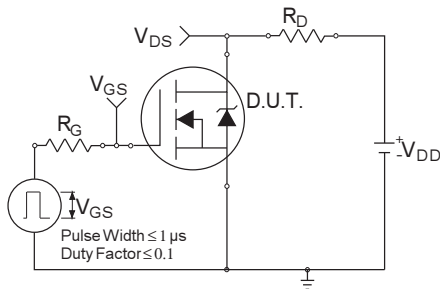
**Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**



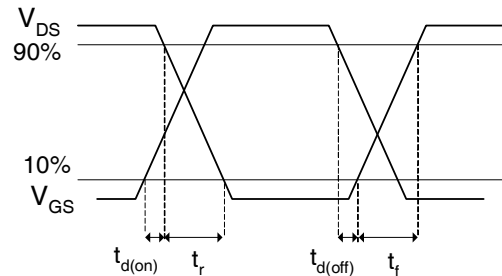
**Fig 16a. Unclamped Inductive Test Circuit**



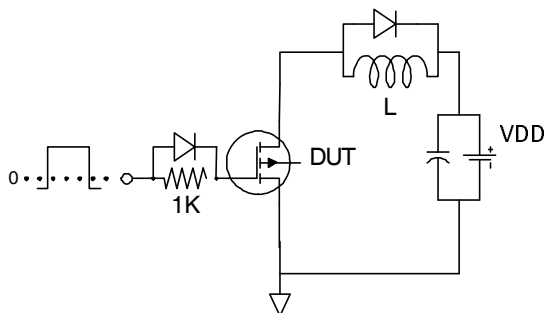
**Fig 16b. Unclamped Inductive Waveforms**



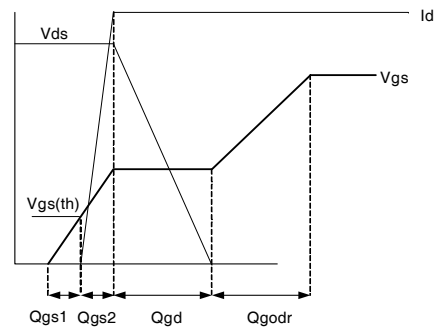
**Fig 17a. Switching Time Test Circuit**



**Fig 17b. Switching Time Waveforms**

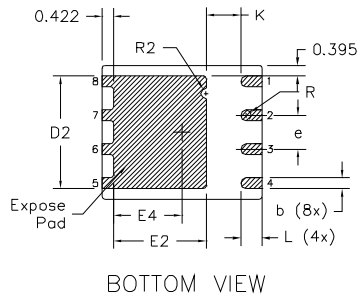
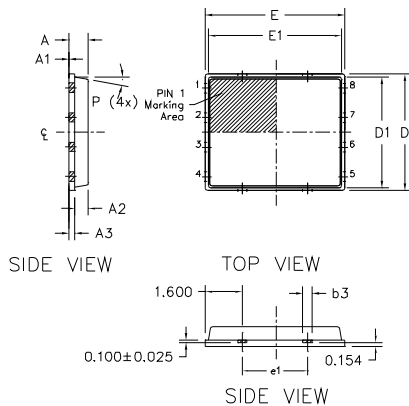


**Fig 18a. Gate Charge Test Circuit**



**Fig 18b. Gate Charge Waveform**

## PQFN 5x6 Outline "B" Package Details

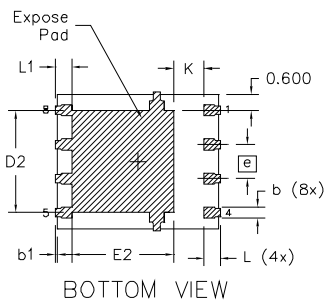
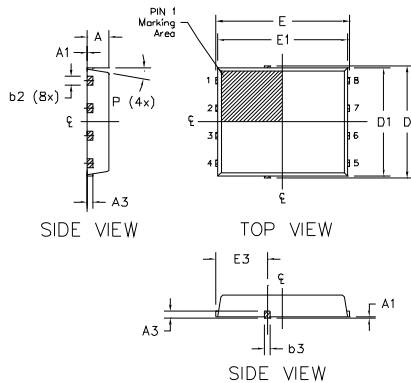


DIM SYMBOL	MILLIMETERS		INCH	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.0315	0.0543
A1	0.000	0.050	0.0000	0.0020
A3	0.200 REF		0.0079 REF	
b	0.350	0.470	0.0138	0.0185
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.150	0.450	0.0059	0.0177
D	5.000 BSC		0.1969 BSC	
D1	4.750 BSC		0.1870 BSC	
D2	4.100	4.300	0.1614	0.1693
E	6.000 BSC		0.2362 BSC	
E1	5.750 BSC		0.2264 BSC	
E2	3.380	3.780	0.1331	0.1488
e	1.270 REF		0.0500 REF	
e1	2.800 REF		0.1102 REF	
K	1.200	1.420	0.0472	0.0559
L	0.710	0.900	0.0280	0.0354
P	0°	12°	0°	12°
R	0.200 REF		0.0079 REF	
R2	0.150	0.200	0.0059	0.0079

**Note:**

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

## PQFN 5x6 Outline "G" Package Details



DIM SYMBOL	MILLIMETERS		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.950	1.050	0.0374	0.0413
A1	0.000	0.050	0.0000	0.0020
A3	0.254 REF		0.0100 REF	
b	0.310	0.510	0.0122	0.0201
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.180	0.450	0.0071	0.0177
D	5.150 BSC		0.2028 BSC	
D1	5.000 BSC		0.1969 BSC	
D2	3.700	3.900	0.1457	0.1535
E	6.150 BSC		0.2421 BSC	
E1	6.000 BSC		0.2362 BSC	
E2	3.560	3.760	0.1402	0.1488
E3	2.270	2.470	0.0894	0.0972
e	1.27 REF		0.050 REF	
K	0.830	1.400	0.0327	0.0551
L	0.510	0.710	0.0201	0.0280
L1	0.510	0.710	0.0201	0.0280
P	10 deg	12 deg	0 deg	12 deg

**Note:**

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

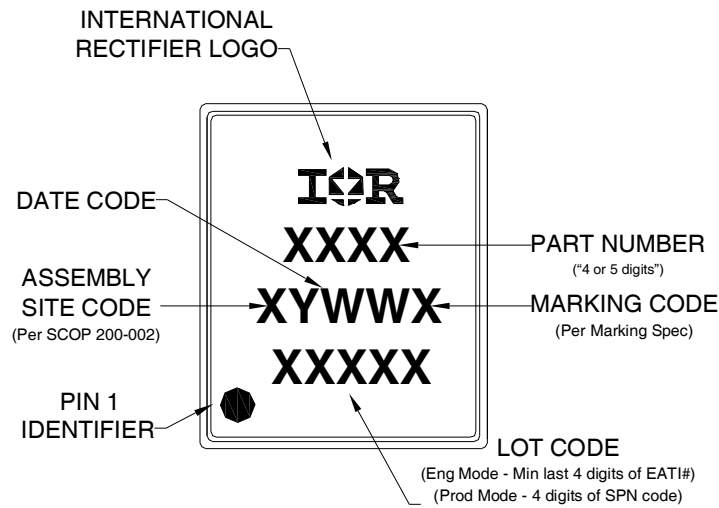
<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

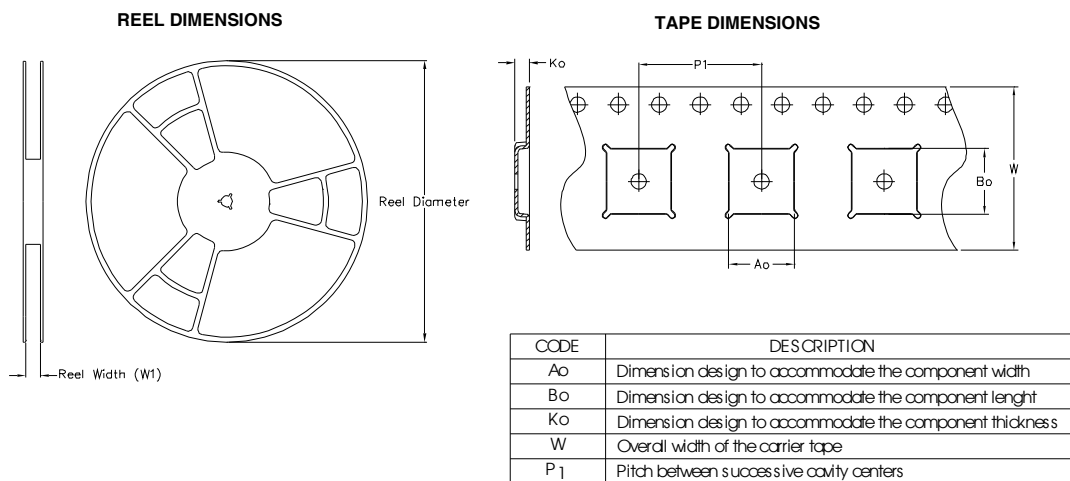
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

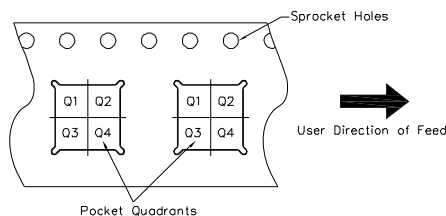
## PQFN 5x6 Part Marking



## PQFN 5x6 Tape and Reel



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



**Qualification information<sup>†</sup>**

Qualification level	Industriid (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier’s web site  
<http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^{\circ}\text{C}$ ,  $L = 1.7\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 30\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_{\theta}$  is measured at  $T_J$  of approximately  $90^{\circ}\text{C}$ .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 100A by production test capability.

**Revision History**

Date	Comments
1/28/2013	• Improve the $R_{\text{dson}}$ at 4.5V max from 1.2m $\Omega$ to 0.99m $\Omega$ .
12/02/2014	• Added $R_{\text{dson}}$ 10V (Absolute Maximum Rating table still based on $R_{\text{dson}}$ max at 4.5V gate drive voltage) on page 1 & 2. • Formatted the data sheet using the IR Corporate template. • Updated ordering information to reflect the End-Of-Life (EOL) of the mini-reel option (EOL notice #259)
4/28/2015	• Updated package outline for “option B” and added package outline for “option G” on page 7 • Updated tape and reel on page 8.
5/19/2015	• Updated package outline for “option G” on page 7. • Updated “IFX logo” on page 1 and page 9.



## Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331